

Supplementary information

High-quality single-crystalline BiSe topological insulator nanowires and nanobelts grown by chemical vapor deposition

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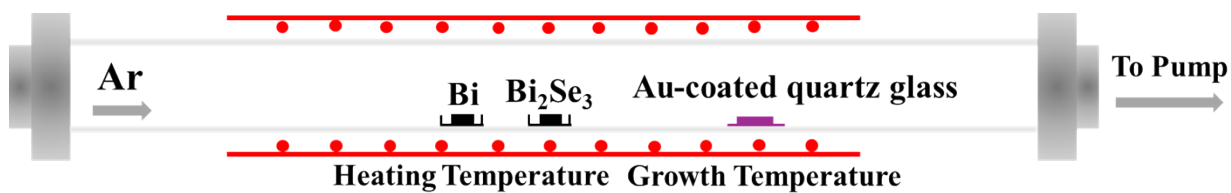


Fig. S1. Schematic diagram of the tube furnace used for the synthesis of BiSe nanowires and the CVD method.

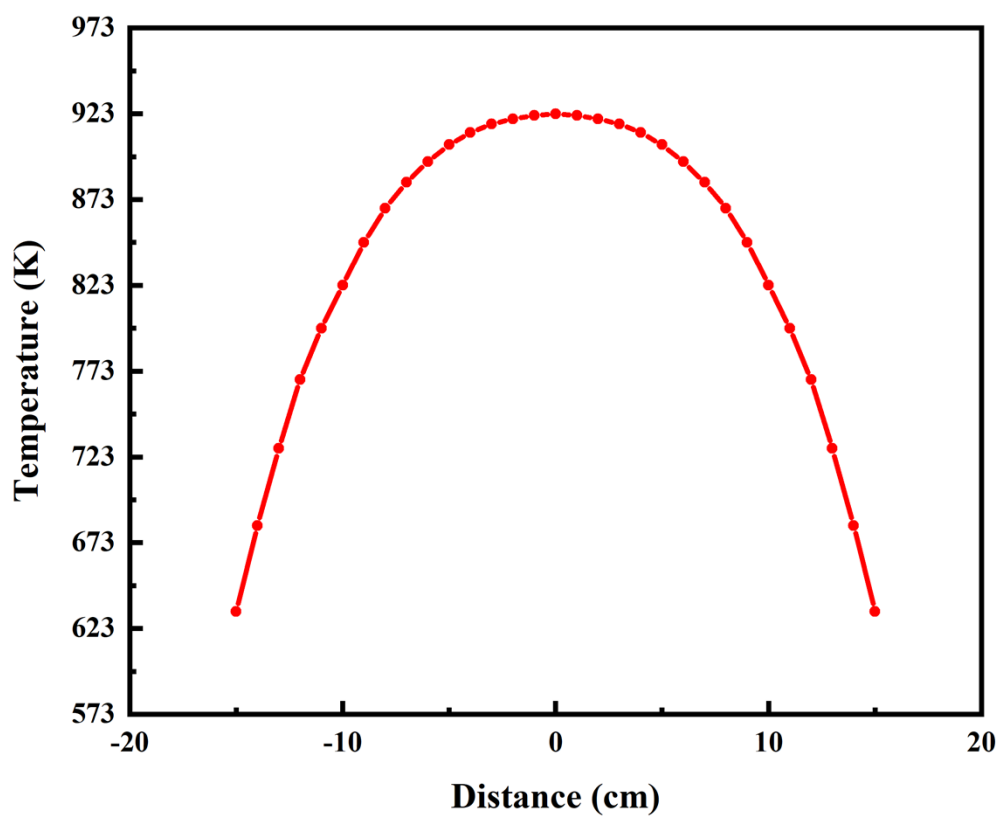


Fig. S2. Temperature distribution curve of tube furnace

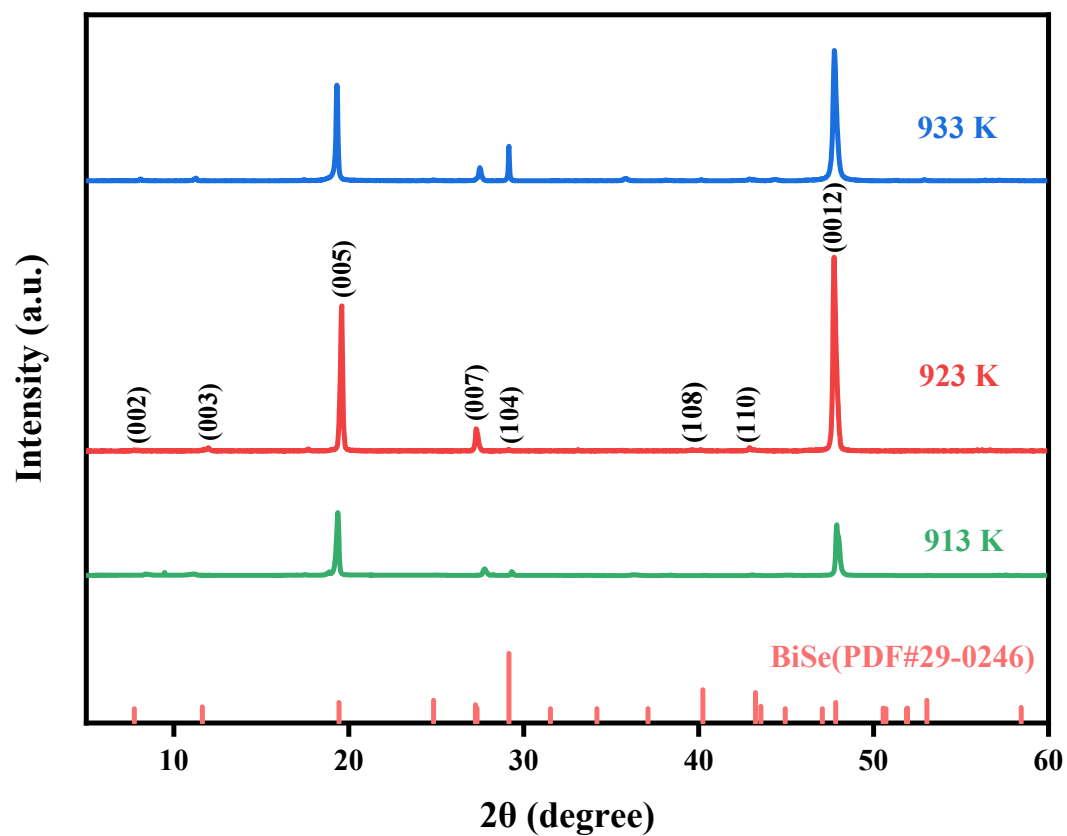


Fig. S3. XRD patterns of BiSe nanowires obtained at different heating temperatures.